20210326002.2 Mar 31, 2021 **PCN Number: PCN Date:** Title: Qualification of MIHO8 as an additional Fab site option for select LBC8 devices Ouality Services **Customer Contact:** PCN Manager Dept: **Estimated Sample** Date provided at **Proposed 1st Ship Date:** Sep 30, 2021 **Availability:** sample request. **Change Type:** Assembly Materials Assembly Site **Assembly Process Electrical Specification** Mechanical Specification Design Packing/Shipping/Labeling Test Process Test Site Wafer Bump Site Wafer Bump Material Wafer Bump Process Wafer Fab Site Wafer Fab Materials Wafer Fab Process Part number change

Notification Details

Description of Change:

Texas Instruments is pleased to announce the qualification of its MIHO8 fabrication facility as an additional Wafer Fab source for the selected devices listed in the "Product Affected" section.

Cu	rrent Fab Sit	e	A	dditional Fab	Site
Current Fab Site	Process	Wafer Diameter	New Fab Site	Process	Wafer Diameter
DP1DM5	LBC8	200mm	MIHO8	LBC8	200mm

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of supply.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas
MIH08	MH8	JPN	Ibaraki

Sample product shipping label (not actual product label)

TEXAS
INSTRUMENTS
MADE IN: Malaysia
2DC: 20:
MSL 2 /260C/1 YEAR SEAL DT

MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT: ITEM: 39

LBL: 5A (L)T0:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$12 (P) (2P) REV: (V) 063317 (20L) CSO: SHE (21L) CCO: USA (20L) ASO: MHE (21L) CCO: USA

Product Affected:

LMR23610AQDDAQ1	LMR23625CFPQDRRRQ1	LMR23630AFQDDAQ1	LMR23630FQDRRRQ1
LMR23610AQDDARQ1	LMR23625CFPQDRRTQ1	LMR23630AFQDDARQ1	LMR23630FQDRRTQ1
LMR23612QDRRRQ1	LMR23625CFQDDAQ1	LMR23630APQDRRRQ1	LMR23630QDRRRQ1
LMR23612QDRRTQ1	LMR23625CFQDDARQ1	LMR23630APQDRRTQ1	LMR23630QDRRTQ1
LMR23615QDRRRQ1	LMR23625CQDDAQ1	LMR23630AQDDAQ1	

LMR23615QDRRTQ1	LMR23625CQDDARQ1	LMR23630AQDDARQ1

Automotive New Product Qualification Summary (As per AEC-Q100, Q006 and JEDEC Guidelines)

Approved 11-20-2019

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as: Number of lots / Total sample size / Total failed										
Туре	e #	Test Spec	Min Lot Qty		SS/L	Lot	Tes	st Name / Condition	Duration	Qual Device LMR23630xQDRRQ1	QBS Process Reference: LM46002AQPWPRQ1
			Te	st Grou	р А -	 Accelerate 	ed Environme	ent Stress Tests			
PC	A1	JEDEC J- STD-020 JESD22- A113	3	All unit	ts for	r A2 to A5		MSL2/260C	-	3/693/0 for A2 to A4 1/45/0 for A5	-
HAS	T A2	JEDEC JESD22- A110	3		77	7	Biased HAST, 130C/85%RH		96 hours	3/231/0	-
AC	А3	JEDEC JESD22- A102	3		77	7		Autoclave 121C	96 hours	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3		77	7	Temp	erature Cycle, -65/150C	500 cycles	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	1		5 un	nits	Temp	erature Cycle, -65/150C	Post 500 cycles	5 units/ 30 wires pass.	•
PTC) A5	JEDEC JESD22- A105	1		45	5	Power Te	mperature Cycle, -40/125C	1000 cycles	1/45/0	-
HTS	L A6	JEDEC JESD22- A103	1		45	5	High T	emp Storage Bake 150C	1000 hours	1/45/0	-
			Te	est Grou	рΒ	- Accelerat	ted Lifetime S	imulation Tests			
	HTOL	B1	JED JESE A1	022-	3	7	77	Life Test, 125C	1000 hours	3/231/0	-
	ELFR	B2	Q100		3	8	00	Early Life Failure Rate, 150C	24 hours	QBS	3/2400/0
	EDR	B3	AE Q100	-005	3		77	NVM Endurance, Data Retention, 150C	1000 hours	QBS	3/231/0
			AE		oup	C – Packag	je Assembly I	ntegrity Tests			
	WBS	C1	Q100	-001	1		30	Wire Bond Shear (Cpk>1.67)	-	1/30/0	-
	WBP	C2	STD Meth	883 nod	1	3	30	Wire Bond Pull (Cpk>1.67)	-	1/30/0	-
	SD	C3	JED JESI B1	022- 02	1	1	15	Surface Mount Solderability >95% Lead Coverage	-	1/15/0	-
	PD	C4	JED JESE B100 B1	022- and 08	3		10	Physical Dimensions (Cpk>1.67)	-	3/30/0	-
F.,	г.	Test Group I		_						0	Fashardan Da : :
TDDB	D1 D2	JESD61 JESD35	-		-	Time De	migration ependent Breakdown				Fechnology Requirements Fechnology Requirements
HCI	D3	JESD60 & 28	-		-		ion Carrier			Completed Per Process 1	Fechnology Requirements
NBTI	D4	-	-		-	Temperatu	ive Bias re Instability			Completed Per Process Technology Requirements	
SM	D5	-	-		-	Stress N	Migration	ligration		Completed Per Process 1	Technology Requirements

		1	Гest G					
НВМ	E2	AEC Q100-002	1	3	ESD - HBM - Q100	2000 Volts	1/3/0	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	750 volts	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-up	125C	1/3/0	-
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0	-

⁻ QBS: Qual By Similarity

A1 (PC): Preconditioning:
Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

AEC-Q006 Table 3a: Integrated Circuit Qualification Test Requirements: Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Qualification Device LMR236xxQDRRQ1 family of devices

Technology attributes covered by this Q006 qualification

- · Silicon attributes : NDA required
- Package family: Small VSON (3x3 mm) from UTAC Thailand
- Wire type: NDA required to read wire type and thickness
- Critical Package materials: NDA required to read Mold compound and die attach

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMR23630xQDDAQ1
est Gro	up A -	Accelerated Environn	nent Stress Test				
	П				SAM Analysis, Pre Stress	-	Passed
PC	A1	JESD22-113	-	-	Preconditioning	Level 3-260C	Passed
			-	-	SAM Analysis, Post-Precon on 11 marked units per lot before THB, TC, PTC and HTSL		Passed : No delamination
HAST	A2	JESD22-A101	3	77	BHAST, Vmax/130C/85% RH	96 Hours	3/231/0
			3	1	Cross Section, Post bHAST 96 Hours	-	3/3/0
			3	11	SAM Analysis, Post bHAST, 96 Hours	-	3/33/0
			3	30	Wire Bond Shear, Post bHAST, 96 Hours	Wires	3/90/0
			3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	3/90/0
			3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	3/90/0
HAST	A2	JESD22-A101	3	70	BHAST, Vmax/130C/85% RH	192 Hours	3/210/0
			3	1	Cross Section, Post bHAST 192 Hours	-	3/3/0
			3	11	SAM Analysis, Post bHAST, 192 Hours	-	3/33/0
			3	30	Wire Bond Shear, Post bHAST, 192 Hours	Wires	3/90/0
			3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	3/90/0
			3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	3/90/0
TC	A4	JESD22-A104	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
			3	1	Cross Section, Post T/C 500 Cycles	-	3/3/0
			3	11	SAM Analysis, PostT/C, 500 Cycles	-	3/33/0
			3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	3/30/0
			3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	3/30/0

			3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	3/30/0
TC	A4	JESD22-A104	3	70	Temperature Cycle, -65/150C	1000 Cycles	3/210/0
			3	1	Cross Section, Post T/C 1000 Cycles	-	3/3/0
			3	11	SAM Analysis, PostT/C, 1000 Cycles	-	3/33/0
			3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/90/0
			3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/90/0
			3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/90/0
PTC	A5	JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	1/45/0
PTC	A5	JESD22-A105	1	45	Power Temperature Cycle	2000 Cycles	1/45/0
HTSL	A6	JESD22-A103	3	45	High Temp Storage Bake 150C	500 Hours	3/135/0
			3	1	Cross Section, Post HTSL 1000 Hours	-	3/3/0
HTSL	A6	JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	3/132/0
			3	1	Cross Section, Post HTSL 2000 Hours	-	3/3/0

- Summary post-reliability construction analysis.

 1. CSAM shows no delamination after BHAST and Temperature cycling

 2. Cross sections showed no evidence of cracking or oxidation within the bonds.

 3. Bond pulls, shears and stitch pulls show no degradation distribution showing similar performance to unaged devices

Automotive Product change Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approved 26-Dec-2019

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition Duration		Qual Device: LMR236xxQDDA	QBS Wafer fab Process Reference: <u>LM4360xxQPWPRQ1</u>	QBS Package Reference: <u>LMR236xxQDDAQ1</u>
		Test Group	A – Acce	elerated E	nvironment Stress Tests				
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning Level 2	260C	QBS	3/693/0	3/693/0
THB	A2	JEDEC JESD22- A101	3	77	Biased Temperature and Humidity, 85C/85%RH	1000 hours	QBS	3/231/0	3/231/0
AC	А3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 hours	QBS	3/231/0	3/231/0
TC	Α4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 cycles	QBS	3/231/0	3/231/0
TC	Α4	Post Temp cycle bond pulls	1	5 units	Post-500 cycles	-	QBS	1/5/0	1/5/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, - 40/125C	1000 cycles	QBS	1/45/0	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 150C	1000 hours	QBS	3/231/0	3/231/0
		Test Group	B-Acce	elerated L	ifetime Simulation Tests		Note 2		
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 150C	408 hours	QBS	3/231/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 hours	QBS	3/2400/0	-
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	1000 hours	QBS	3/231/0	-
		Test Gro	up C – Pa	ckage As	sembly Integrity Tests				
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	-	QBS	-	1/30/0

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMR236xxQDDA	QBS Wafer fab Process Reference: LM4360xxQPWPRQ1	QBS Package Reference: <u>LMR236xxQDDAQ1</u>
WBF	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull (Cpk>1.67)	-	QBS	-	1/30/0
SD	СЗ	JEDEC JESD22- B102	1	15	Auto Solderability (Pb and Pb- Free)	>95% Lead Coverage	QBS	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Auto Physical Dimensions	Cpk>1.33 Ppk>1.67	QBS	-	3/30/0
		Test Gr	oup D – C	Die Fabrica	ation Reliability Tests				
EM	D1	JESD61	-	-	Electro-migration	-		er Process Technology equirements	-
TDDE	D2	JESD35	-	-	Time Dependent Dielectric Completed Per Process Technology Breakdown Requirements		-		
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	Hot Injection Carrier - Completed Per Process Technology Requirements			-
NBT	D4	-	-	-	Negative Bias Temperature Instability	-		er Process Technology equirements	-
SM	D5	-	-	-	Stress Migration	-		er Process Technology equirements	-
		Test	Group E -	 Electrica 	l Verification Tests				
НВМ	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0	-	
CDM	E3	AEC Q100-011	1	3	ESD - CDM	750 V	1/3/0	-	
LU	E4	AEC Q100-004	1	6	Latch-up	125C	1/6/0	-	
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/30/0	-	

⁻ QBS: Qual By Similarity

Note 1: Top metallization of the silicon die is the same process and same factory location for both primary and second sourced fab products – supports QBS for group A and group C tests.

Note 2: Silicon IP components of the LMR232xxQDDA are used in LM4360xxQPWPRQ1

A1 (PC): Preconditioning:
Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level: Grade 1 (or Q): -40°C to +125°C E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED

Room/Hot: THB/HAST, TC/PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

ADDENDUM A: AEC-Q006 Table 3a: Integrated Circuit Qualification Test Requirements: Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Qualification Device LMR236xxQDDA family of devices

Technology attributes covered by this Q006 qualification

- Silicon attributes: Same silicon technology and top side metallization
- Package family: HSOIC (PSOP) from ASE Shanghai, China
- Wire type: NDA information
- Critical Package materials: NDA information

⁻ Qual Device LMR236xxQDDARQ1 is qualified at LEVEL2-260CG

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: LMR23630AQDDAQ1
Test G	roup	A - Accelerated	Environment S	tress Tes	st		
					SAM Analysis, Pre Stress	-	Passed
PC	A1	JESD22-113	-	-	Preconditioning	Level 2-260C	3/738/0
			-	-	SAM Analysis, Post-Precon	-	Passed
HAST	A2	JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0
			3	1	Cross Section, Post bHAST 96 Hours	-	3/3/0
			3	11	SAM Analysis, Post bHAST, 96 Hours	-	3/33/0
			3	30	Wire Bond Shear, Post bHAST, 96 Hours	Wires	3/90/0
			3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	3/90/0
			3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	3/90/0
HAST	A2	JESD22-A110	3	70	Biased HAST, 130C/85%RH	192 Hours	3/210/0
			3	1	Cross Section, Post bHAST 192 Hours	-	3/3/0
			3	11	SAM Analysis, Post bHAST, 192 Hours	-	3/33/0
			3	30	Wire Bond Shear, Post bHAST, 192 Hours	Wires	3/90/0
			3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	3/90/0
			3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	3/90/0
TC	A4	JESD22-A104	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
			3	1	Cross Section, Post T/C 500 Cycles	-	3/3/0
			3	11	SAM Analysis, Post T/C, 500 Cycles	-	3/33/0
			3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	3/90/0
			3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	3/90/0
			3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	3/90/0
TC	A4	JESD22-A104	3	70	Temperature Cycle, -65/150C	1000 Cycles	3/210/0
			3	1	Cross Section, Post T/C 1000 Cycles	-	3/3/0
			3	11	SAM Analysis, Post T/C, 1000 Cycles	-	3/33/0
			3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/90/0
			3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/90/0
			3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/90/0
PTC	A5	JESD22-A105	1	45	Power Temperature Cycle 1000 Cycles 1/45/0		1/45/0
PTC	A5	JESD22-A105	1	45	Power Temperature Cycle 2000 Cycles 1/-		1/45/0
HTSL	A6	JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	3/135/0
			3	1	Cross Section, Post HTSL 1000 Hours	-	3/3/0
HTSL	A6	JESD22-A103	3	45	High Temp Storage Bake 150C	2000 Hours	3/132/0
	П		3	1	Cross Section, Post HTSL 2000 Hours	-	3/3/0

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, PTC & TC samples, as applicable.

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

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